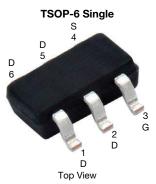
Vishay Siliconix

Automotive P-Channel 12 V (D-S) 175 °C MOSFET



Marking Code: 8UY

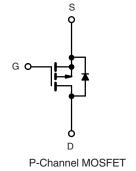
PRODUCT SUMMARY					
V _{DS} (V)	-12				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.025				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.032				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -1.8 \text{ V}$	0.043				
I _D (A)	-8				
Configuration	Single				

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified c
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912







ORDERING INFORMATION					
Package	TSOP-6				
Lead (Pb)-free and halogen-free	SQ3461EV (for detailed order number please see www.vishay.com/doc?79771)				

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-12	M	
Gate-source voltage		V_{GS}	± 8	V	
Continuous drain current ^c	T _C = 25 °C	1	-8		
	T _C = 125 °C	I _D	-6.6		
Continuous source current (diode conduction)		I _S	-6.3	Α	
Pulsed drain current ^a		I _{DM}	-30		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-17		
Single pulse avalanche energy	L = U.1 MH	E _{AS}	14	mJ	
Manian and a single state of 2	T _C = 25 °C	В	5	W	
Maximum power dissipation ^a	T _C = 125 °C	P_{D}	1.67		
Operating junction and storage temperature	e range	T _J , T _{sta}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	LIMIT	UNIT				
Junction to ambient	PCB mount b	R_{thJA}	110	°C/W			
Junction to case (drain)		R_{thJF}	30	C/VV			

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. Package limited



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static	•	•					
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-12	-	-	.,
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = -250 μA		-0.6	-1	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	V _{DS} = 0 V, V _{GS} = ± 8 V		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = -12 V	-	-	-1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -12 V, T _J = 125 °C	-	-	-50	μA
		V _{GS} = 0 V	V _{DS} = -12 V, T _J = 175 °C	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -4.5 V	V _{DS} = -5 V	-11	-	-	Α
		V _{GS} = -4.5 V	I _D = -7.9 A	-	0.021	0.025	
		V _{GS} = -4.5 V	I _D = -6.6 A, T _J = 125 °C	-	-	0.033	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -3.5 A, T _J = 175 °C	-	-	0.037	Ω
		V _{GS} = -2.5 V	I _D = -7 A	-	0.026	0.032	
		V _{GS} = -1.8 V	I _D = -3 A	-	0.036	0.043	
Forward Transconductance b	9 _{fs}	V _{DS} = -5 V, I _D = -7.9 A		-	21	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	1600	2000	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 V$ $V_{DS} = -6 V, f = 1 MHz$		620	770	рF
Reverse Transfer Capacitance	C _{rss}			-	490	620	1
Total Gate Charge ^c	Q_g			-	21	28	
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = -4.5 \text{ V}$	$V_{GS} = -4.5 \text{ V}$ $V_{DS} = -6 \text{ V}, I_D = -7.9 \text{ A}$		2.5	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	7	-	
Gate Resistance	R_g	f = 1 MHz		2.8	5.7	8.6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	17	
Rise Time ^c	t _r	$V_{DD} = -6 \text{ V}, \text{ R}_{L} = 1.6 \Omega$ $I_{D} \cong -7.9 \text{ A}, \text{ V}_{GEN} = -4.5 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	52	68	- ns
Turn-Off Delay Time ^c	t _{d(off)}			1	92	120	
Fall Time ^c	t _f			-	71	93	
Source-Drain Diode Ratings and Chara	cteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	-20	Α
Forward Voltage	V_{SD}	I _F = -2 A, V _{GS} = 0 V			-0.8	-1.2	V

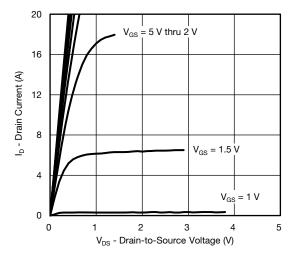
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

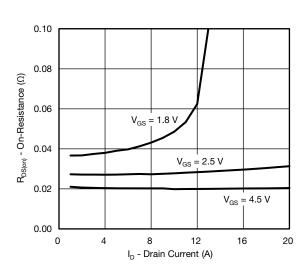
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



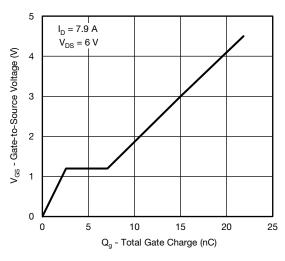
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



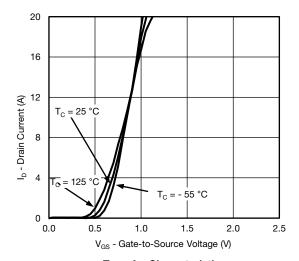
Output Characteristics



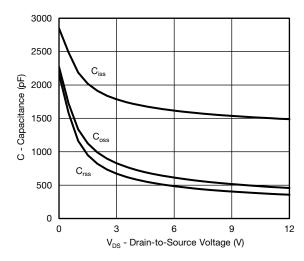
On-Resistance vs. Drain Current



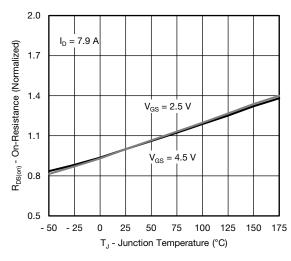
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature



0.5

0.3

0.1

- 0.1

- 0.3

- 0.5

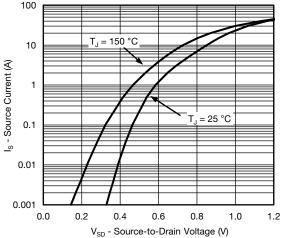
- 50 - 25

0

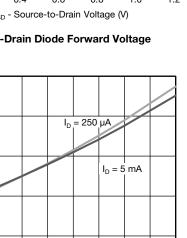
25 50 75 100

V_{GS(th)} Variance (V)

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



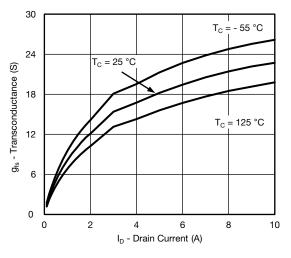
Source-Drain Diode Forward Voltage



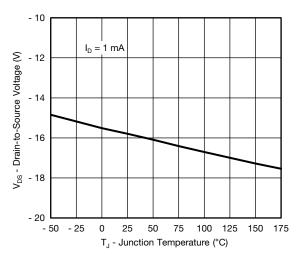
125 150 175

Threshold Voltage

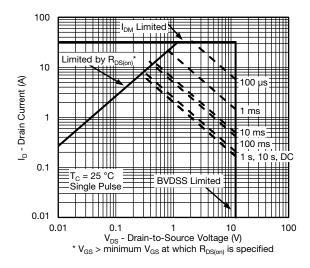
T_J - Temperature (°C)



Transconductance



Drain-to- Source Voltage vs. Junction Temperature





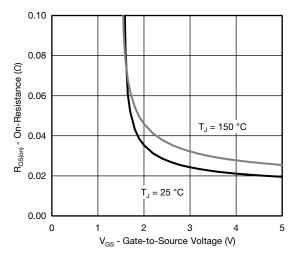


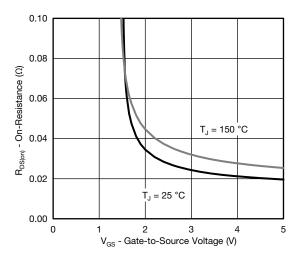
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Safe Operating Area



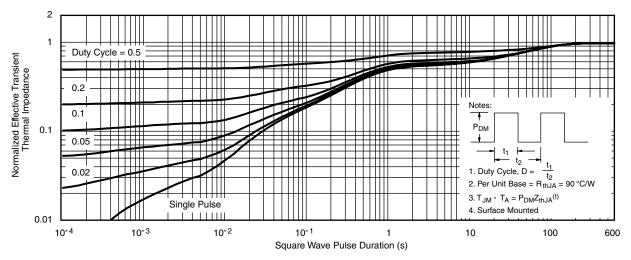
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





On-Resistance vs. Gate-to-Source Voltage (7.9 A)

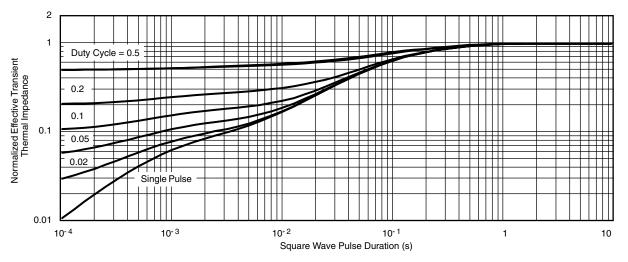
On-Resistance vs. Gate-to-Source Voltage (6.6 A)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions.

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

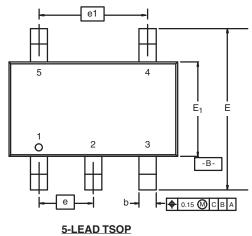
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262994.

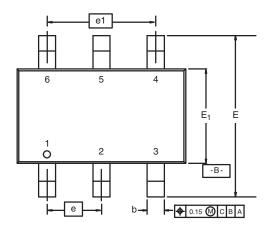




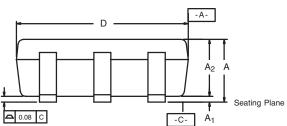
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C

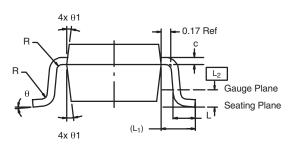




5-LEAD ISOP







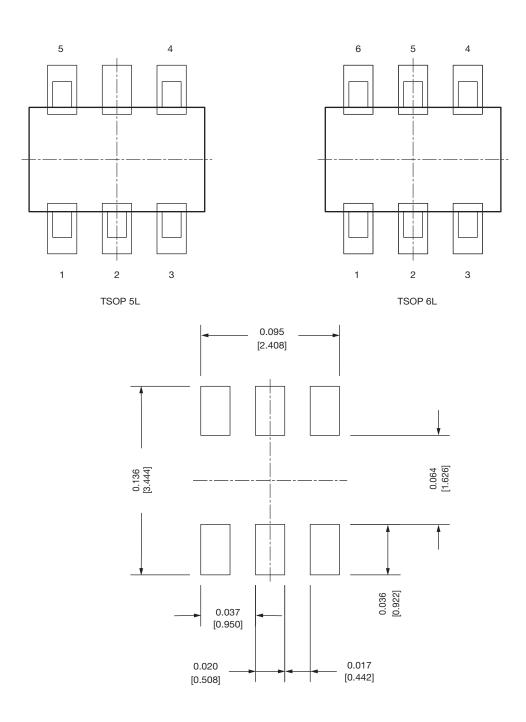
	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁	0.60 Ref				0.024 Ref		
L ₂	0.25 BSC				0.010 BSC		
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom				7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

DWG: 5540

Document Number: 71200 18-Dec-06



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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